









# **CEM0415**

#### 150V Δ 62mΩ Δ 4A Δ Si MOSFET

SILICON Si MOSFET ▲ SMD type

N-channel enhancement mode

UL94V-0 rated flame retardant epoxy

SO8 package ▲ MSL 3

Super high dense cell density for extremely low R<sub>DS(ON)</sub> **High power and current handling capability** 

#### **MAXIMUM RATINGS**

Parameter (T <sub>A</sub> = 25°C, unless otherwise noted)		Characteristics
Drain-Source Voltage	V <sub>DS</sub>	150V
Gate-Source Voltage	V <sub>GS</sub>	±30V
Continuous Drain Current	I <sub>D</sub>	4A
Pulsed Drain Current Note 1	I <sub>DM</sub>	16A
Maximum Power Dissipation	P <sub>D</sub>	2.5W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55°C to +150°C

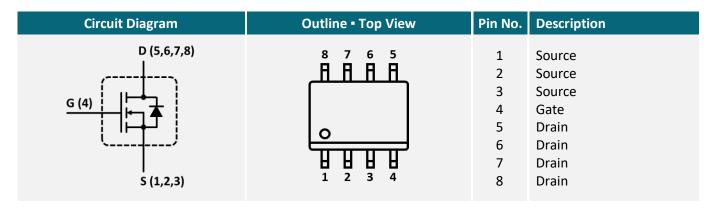
#### THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R <sub>TH_JA</sub>	50°C/W

# **APPLICATIONS**

Audio	Industrial	Power over	Power	UPS
Amplifier	Control	Ethernet	Inverter	
		PoE		

### **PIN DESCRIPTION**





# **ELECTRICAL CHARACTERISTICS** ▲ T<sub>A</sub> = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	$BV_{DSS}$		150		V
Zero Gate Voltage Drain Current	$V_{DS} = 135V, V_{GS} = 0V$	I <sub>DSS</sub>			1	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 30V$ , $V_{DS} = 0V$	I <sub>GSSF</sub>			100	nA
Gate Body Leakage Current, Reverse	$V_{GS}$ = -30V, $V_{DS}$ = 0V	$I_{GSSR}$			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}$ , $I_{D} = 250 \mu A$	$V_{GS(th)}$	2		4	V
Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 3.3A$	R <sub>DS(ON)</sub>		62	85	mΩ
Static Drain-Source On-Resistance	$V_{GS} = 6V$ , $I_D = 3A$	R <sub>DS(ON)</sub>		70	95	mΩ
Gate Input Resistance	f = 1MHz, Open Drain	R <sub>G</sub>		1		Ω
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	C <sub>ISS</sub>		1355		pF
Output Capacitance	$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	Coss		130		pF
Reverse Transfer Capacitance	$V_{DS} = 30V$ , $V_{GS} = 0V$ , $f = 1MHz$	$C_{RSS}$		50		pF
Switching Characteristics Note 4						
Turn-On Delay Time	$V_{DD} = 75V$ , $V_{GS} = 10V$ , $I_D = 3.5A$ , $R_{G(ext)} = 6\Omega$	t <sub>D(ON)</sub>		18		ns
Turn-On Rise Time	$V_{DD} = 75V$ , $V_{GS} = 10V$ , $I_D = 3.5A$ , $R_{G(ext)} = 6\Omega$	$t_{R}$		5	10	ns
Turn-Off Delay Time	$V_{DD} = 75V$ , $V_{GS} = 10V$ , $I_D = 3.5A$ , $R_{G(ext)} = 6\Omega$	t <sub>D(OFF)</sub>		35		ns
Turn-Off Fall Time	$V_{DD}$ = 75V, $V_{GS}$ = 10V, $I_D$ = 3.5A, $R_{G(ext)}$ = $6\Omega$	t <sub>F</sub>		5	10	ns
Total Gate Charge	$V_{DS} = 75V$ , $V_{GS} = 10V$ , $I_D = 3.5A$	$Q_{G}$		23		nC
Gate Source Charge	$V_{DS} = 75V$ , $V_{GS} = 10V$ , $I_{D} = 3.5A$	Q <sub>GS</sub>		5		nC
Gate Drain Charge	$V_{DS} = 75V$ , $V_{GS} = 10V$ , $I_{D} = 3.5A$	$\mathbf{Q}_{GD}$		6		nC
<b>Drain-Source Diode Characteristics a</b>	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		Is			2	Α
Drain-Source Diode Forward Voltage Note 3	$V_{GS} = 0V$ , $I_S = 2A$	$V_{SD}$			1.2	V

#### Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

2: Surface Mounted on FR4 Board, t ≤ 10 sec

3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

4: Guaranteed by design, not subject to production testing.



#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



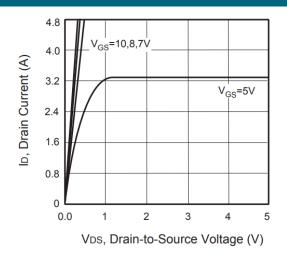


Fig. 2 • Transfer Characteristics

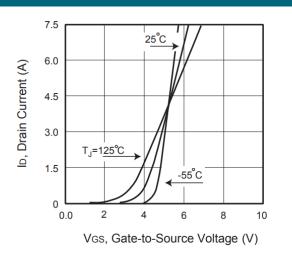


Fig. 3 • Capacitance

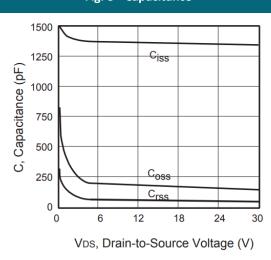


Fig. 4 • On-Resistance Variation with Temperature

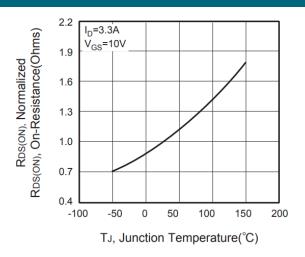


Fig. 5 • Gate Threshold Variation with Temperature

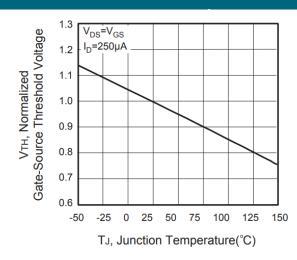
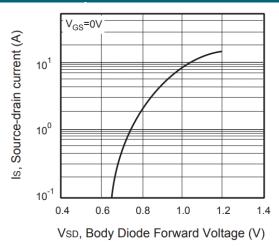


Fig. 6 • Body Diode Forward Voltage Variation with Source Current



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#### REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

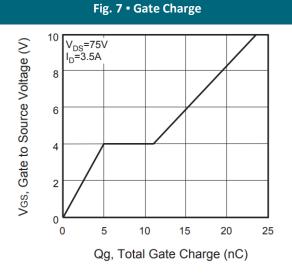
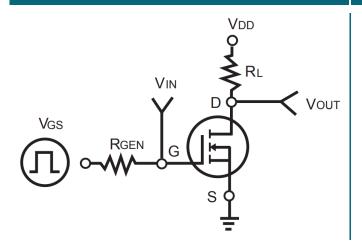


Fig. 8 • Maximum Safe Operating Area

Fig. 9 • Switching Test Circuit

Fig. 10 • Switching Waveforms

VDS, Drain-Source Voltage (V)



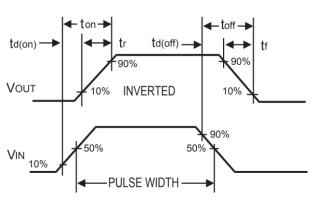
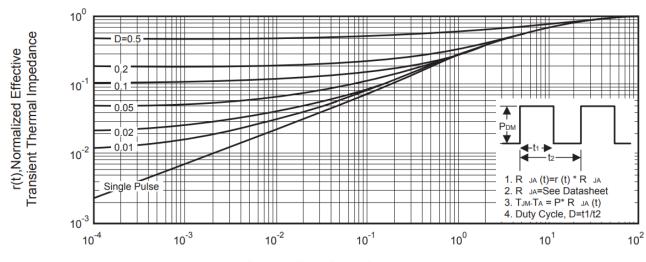


Fig. 11 - Normalized Thermal Transient Impedance Curve

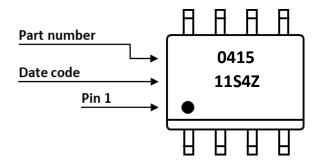


Square Wave Pulse Duration (sec)

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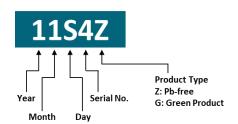


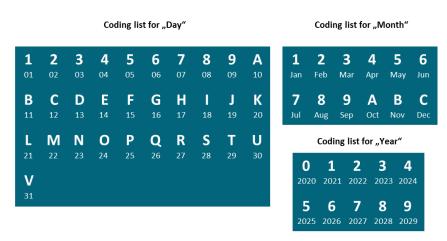
#### **PART MARKING**



# **DATE CODE**

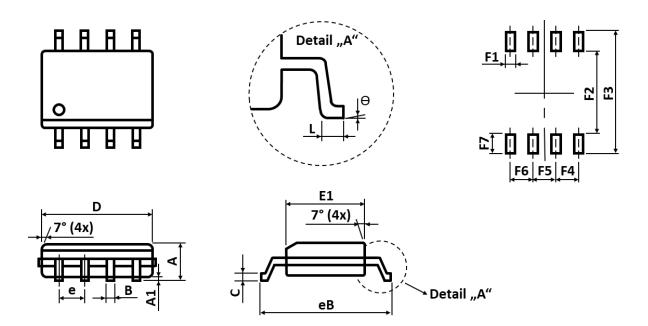
Example: 11S4Z







# PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	1.350	-	1.750
A1	0.100	-	0.250
В	0.310	-	0.510
С	0.170	-	0.250
D	4.690	-	5.000

Sym	Millimeters Millimeters (Min.) (Typ.)		Millimeters (Max.)
E1	3.700		4.060
еВ	5.800		6.200
е		1.270	
L	0.400		0.950
Θ	0°	-	8°

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	_	0.500	_
F2	-	4.250	-
F3	-	6.250	-
F4	-	1.270	-

(Min.)	(Typ.)	Millimeters (Max.)
-	1.270	-
-	1.270	-
-	1.000	-
	(Min.) - - -	- 1.270 - 1.270

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

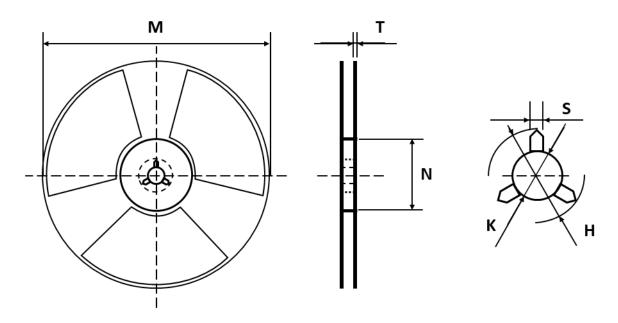
2. For further information, please reference document IPC-7351A.

# **ORDERING INFORMATION**

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEM0415	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs

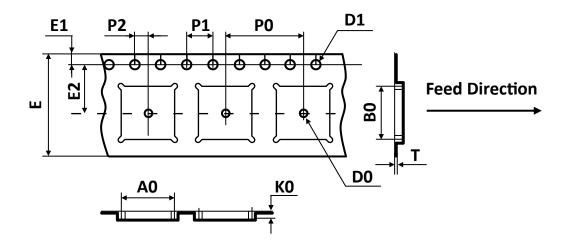


# **REEL DIMENSIONS** ▲ All dimensions in mm



Tape Size	Reel Size	M	N	Т	Н	K	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
12mm	<b>9</b> 550	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

# **TAPE DIMENSIONS** ▲ All dimensions in mm

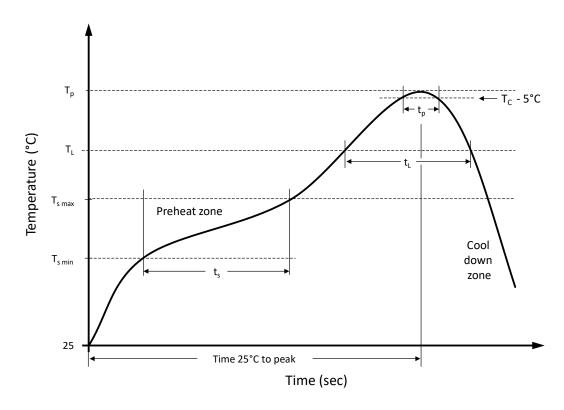


Package	Α0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	T
SO8	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
308	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



# RECOMMENDED REFLOW SOLDERING PROFILE



# **Recommended reflow soldering conditions** ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T <sub>s max</sub>	150 °C	200 °C
Preheat time t <sub>s</sub> from T <sub>s min</sub> to T <sub>s max</sub>	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	$T_L$	183 °C	217 °C
Time t <sub>L</sub> maintained above T <sub>L</sub>	t <sub>L</sub>	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t <sub>p</sub>	20 seconds max.	30 seconds max.
Ramp-down rate (T <sub>L</sub> to T <sub>p</sub> )		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



#### **REVISION TABLE**

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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